



**PATENT**  
Atty. Dkt. No. AMAT/2966P2/DD/BCVD/JW

2823

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:  
Huang

**Serial No.: 09/270,039**

Confirmation No.: 0424

**Filed: March 16, 1999**

For: **IN SITU DEPOSITION OF A  
LOW K DIELECTRIC LAYER,  
BARRIER LAYER, ETCH  
STOP, AND ANTI-  
REFLECTIVE COATING FOR  
DAMASCENE APPLICATION**

**Group Art Unit: 2823**

**Examiner: G. FOURSON**

Assistant Commissioner for Patents  
Washington, D.C. 20231

**Dear Sir:**

**CERTIFICATE OF MAILING**  
**37 CFR 1.8**

I hereby certify that this correspondence is being deposited on  
5/24, 2001 with the United States Postal Service as  
First Class Mail in an envelope addressed to: Assistant  
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5/24/01                      Kurt Z. Fisher  
Date                                      Signature

**RESPONSE TO RESTRICTION REQUIREMENT DATED APRIL 24, 2001**

In response to the Office Action dated April 24, 2001, having a shortened statutory period for response set to expire on May 24, 2001, the Applicants elect claims 14-29. Please enter the following amendments and reconsider the restriction pending in the application for reasons discussed below.

**IN THE CLAIMS:**

**Please cancel claim 5, and amend the claims as follows:**

1. (Amended) A substrate, comprising:
  - a silicon carbide layer having a dielectric constant less than 7.0 and deposited on the substrate;
  - a first dielectric layer deposited on the silicon carbide layer *in situ* with the silicon carbide layer; and
  - a photoresist layer deposited on the first dielectric layer.